

In the Abstract:

~~Method for oxidizing a layer, and associated holding devices for a substrate~~

~~The invention explains, inter alia, a~~ A method is presented in which a layer which is to be oxidized is processed, preferably in a single-substrate process, ~~t.~~ The process temperature during the processing being is recorded directly at the substrate (114) or at a holding device (110) for the substrate. It ~~is possible to produce oxide layers with an accurately predetermined oxide width.~~ The method includes introducing a substrate, which bears a layer to be oxidized uncovered in an edge region in a layer stack, into a heating device, passing an oxidation gas onto the substrate, heating the substrate to a process temperature, which is recorded during the processing via a temperature of a holding device which holds the substrate, and controlling the substrate temperature to a desired temperature or temperature curve during the processing.

~~(Figure 3)~~